

BF398 is PNP silicon transistor designed for high voltage applications.

TO-92F



CBE

ABSOLUTE MAXIMUM RATINGS

Collector-Base Voltage	VCBO	150V
Collector-Emitter Voltage	VCEO	150V
Emitter-Base Voltage	VEBO	6V
Total Power Dissipation	Ptot	625mW
Collector Current	IC	100mA
Operating Junction & Storage Temperature	Tj, Tstg	-55 to +150°C

ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN	MAX	UNIT	TEST CONDITIONS
Collector-Base Breakdown Voltage	BVCBO	150		V	IC=10μA IE=0
Collector-Emitter Breakdown Voltage	LVCEO	150		V	IC=10mA IB=0
Emitter-Base Breakdown Voltage	BVEBO	6		V	IE=10μA IC=0
Collector Cutoff Current	ICBO		50	nA	VCB=100V IE=0
Emitter Cutoff Current	IEBO		50	nA	VEB=4V IC=0
D.C. Current Gain	HFE	25			IC=1mA VCE=10V
		30	200		IC=10mA VCE=10V
		20			IC=100mA VCE=10V
Base-Emitter Saturation Voltage	VBE(sat)	0.6	0.9	V	IC=10mA IB=1mA
Collector-Emitter Saturation Voltage	VCE(sat)		0.5	V	IC=10mA IB=1mA



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Datasheets for electronics components.